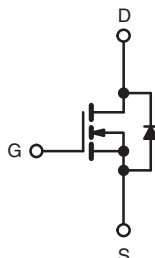
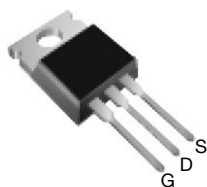


## D Series Power MOSFET

### PRODUCT SUMMARY

|                                         |                 |     |
|-----------------------------------------|-----------------|-----|
| $V_{DS}$ (V) at $T_J$ max.              | 550             |     |
| $R_{DS(on)}$ max. at 25 °C ( $\Omega$ ) | $V_{GS} = 10$ V | 0.4 |
| $Q_g$ max. (nC)                         | 58              |     |
| $Q_{gs}$ (nC)                           | 8               |     |
| $Q_{gd}$ (nC)                           | 14              |     |
| Configuration                           | Single          |     |

**TO-220AB**


N-Channel MOSFET

### FEATURES

- Optimal Design
  - Low Area specific On-Resistance
  - Low Input Capacitance ( $C_{iss}$ )
  - Reduced Capacitive Switching Losses
  - High Body Diode Ruggedness
  - Avalanche Energy Rated ( $U_{IS}$ )
- Optimal Efficiency and Operation
  - Low Cost
  - Simple Gate Drive Circuitry
  - Low Figure-Of-Merit (FOM):  $R_{on} \times Q_g$
  - Fast Switching
- Material categorization: For definitions of compliance please see [www.vishay.com/doc?99912](http://www.vishay.com/doc?99912)

### Note

\* Lead (Pb)-containing terminations are not RoHS-compliant. Exemptions may apply.

### APPLICATIONS

- Consumer Electronics
  - Displays (LCD or Plasma TV)
- Server and Telecom Power Supplies
  - SMPS
- Industrial
  - Welding, Induction Heating, Motor Drives
- Battery Chargers



**RoHS\***  
COMPLIANT  
HALOGEN  
**FREE**  
Available

### ORDERING INFORMATION

|                                 |                |
|---------------------------------|----------------|
| Package                         | TO-220AB       |
| Lead (Pb)-free                  | SiHP14N50D-E3  |
| Lead (Pb)-free and Halogen-free | SiHP14N50D-GE3 |

### ABSOLUTE MAXIMUM RATINGS ( $T_C = 25$ °C, unless otherwise noted)

| PARAMETER                                        | SYMBOL           | LIMIT          | UNIT |
|--------------------------------------------------|------------------|----------------|------|
| Drain-Source Voltage                             | $V_{DS}$         | 500            | V    |
| Gate-Source Voltage                              | $V_{GS}$         | $\pm 30$       |      |
| Gate-Source Voltage AC ( $f > 1$ Hz)             |                  | 30             |      |
| Continuous Drain Current ( $T_J = 150$ °C)       | $V_{GS}$ at 10 V | $T_C = 25$ °C  | A    |
|                                                  |                  | $T_C = 100$ °C |      |
| Pulsed Drain Current <sup>a</sup>                | $I_{DM}$         | 38             | W/°C |
| Linear Derating Factor                           |                  | 1.6            |      |
| Single Pulse Avalanche Energy <sup>b</sup>       | $E_{AS}$         | 56             | mJ   |
| Maximum Power Dissipation                        | $P_D$            | 208            | W    |
| Operating Junction and Storage Temperature Range | $T_J, T_{stg}$   | - 55 to + 150  | °C   |
| Drain-Source Voltage Slope                       | $dV/dt$          | 24             | V/ns |
| Reverse Diode $dV/dt$ <sup>d</sup>               |                  | 0.4            |      |
| Soldering Recommendations (Peak Temperature)     | for 10 s         | 300°           | °C   |

### Notes

- Repetitive rating; pulse width limited by maximum junction temperature.
- $V_{DD} = 50$  V, starting  $T_J = 25$  °C,  $L = 2.3$  mH,  $R_g = 25$   $\Omega$ ,  $I_{AS} = 7$  A.
- 1.6 mm from case.
- $I_{SD} \leq I_D$ , starting  $T_J = 25$  °C.

**THERMAL RESISTANCE RATINGS**

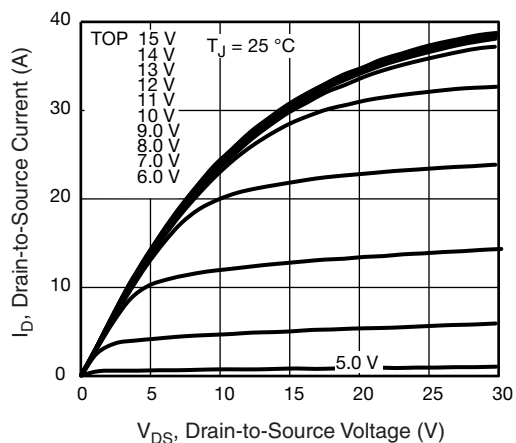
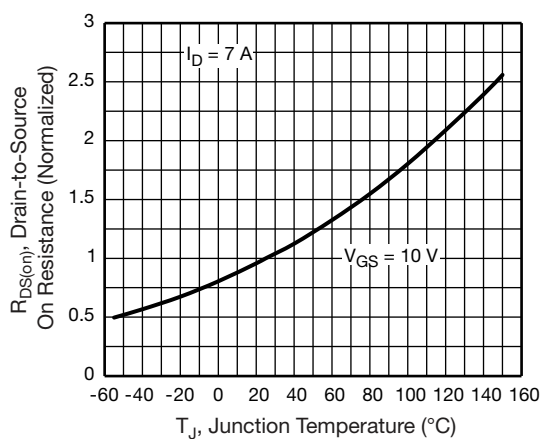
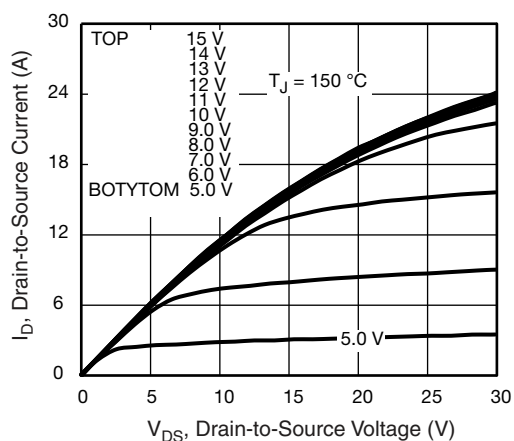
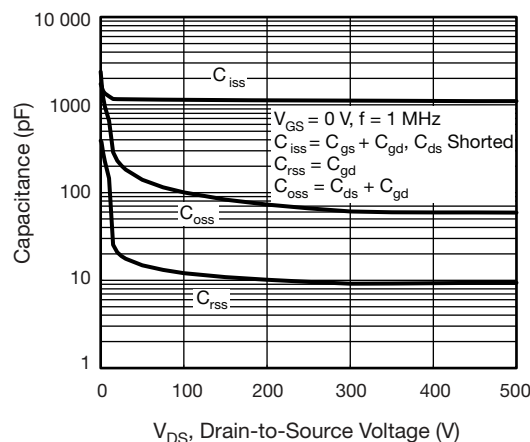
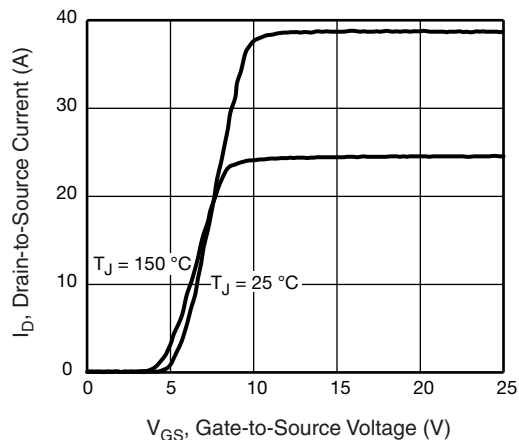
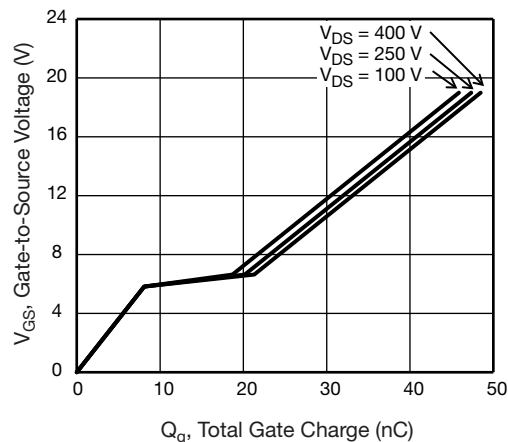
| PARAMETER                        | SYMBOL     | TYP. | MAX. | UNIT |
|----------------------------------|------------|------|------|------|
| Maximum Junction-to-Ambient      | $R_{thJA}$ | -    | 62   | °C/W |
| Maximum Junction-to-Case (Drain) | $R_{thJC}$ | -    | 0.6  |      |

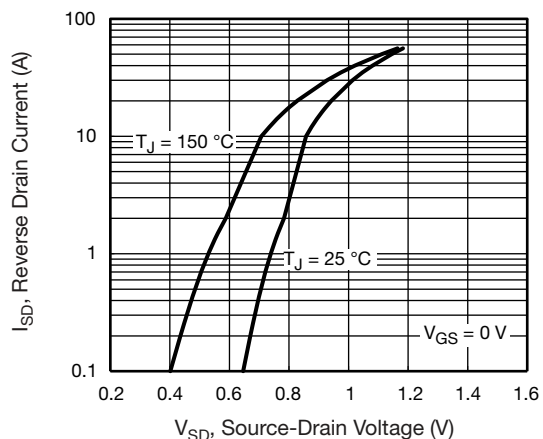
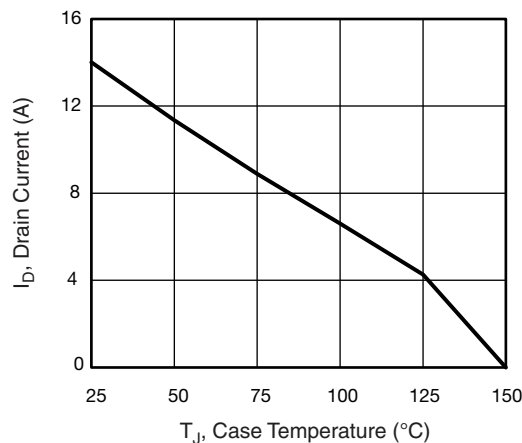
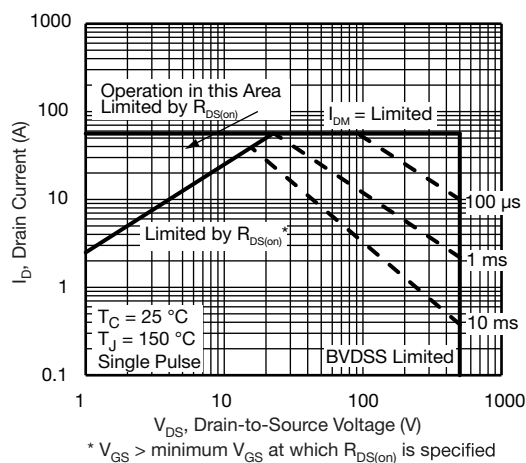
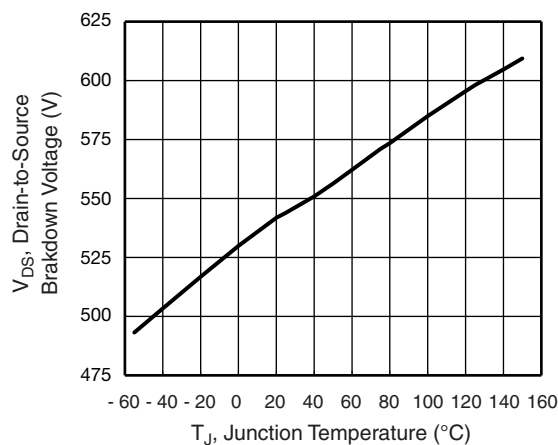
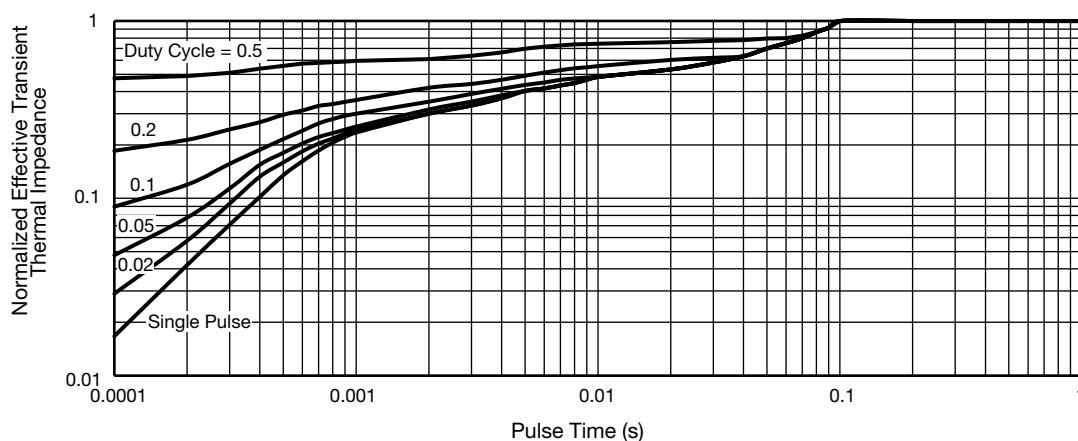
**SPECIFICATIONS** ( $T_J = 25\text{ °C}$ , unless otherwise noted)

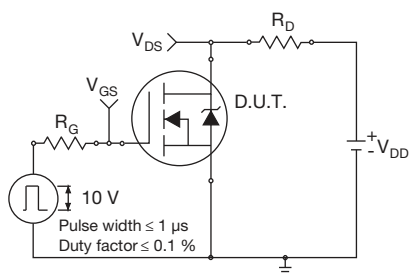
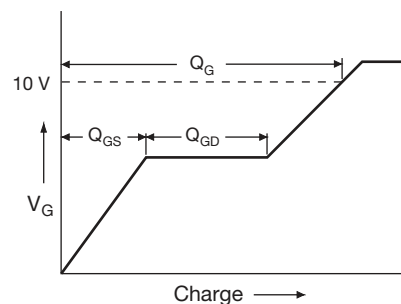
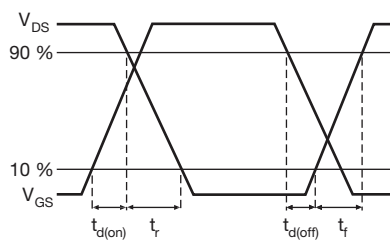
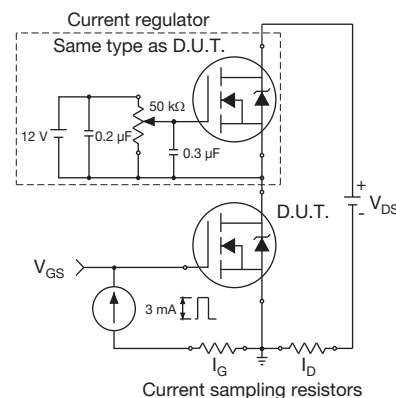
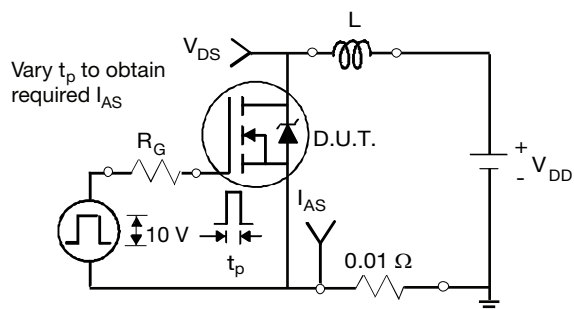
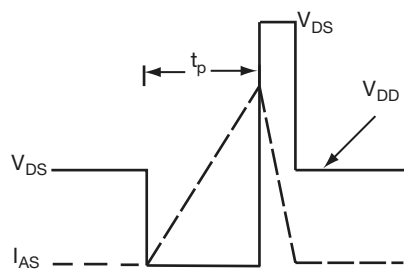
| PARAMETER                                                 | SYMBOL              | TEST CONDITIONS                                                                                                                                       | MIN. | TYP.  | MAX.      | UNIT          |
|-----------------------------------------------------------|---------------------|-------------------------------------------------------------------------------------------------------------------------------------------------------|------|-------|-----------|---------------|
| <b>Static</b>                                             |                     |                                                                                                                                                       |      |       |           |               |
| Drain-Source Breakdown Voltage                            | $V_{DS}$            | $V_{GS} = 0\text{ V}$ , $I_D = 250\text{ }\mu\text{A}$                                                                                                | 500  | -     | -         | V             |
| $V_{DS}$ Temperature Coefficient                          | $\Delta V_{DS}/T_J$ | Reference to $25\text{ °C}$ , $I_D = 250\text{ }\mu\text{A}$                                                                                          | -    | 0.58  | -         | V/°C          |
| Gate Threshold Voltage (N)                                | $V_{GS(th)}$        | $V_{DS} = V_{GS}$ , $I_D = 250\text{ }\mu\text{A}$                                                                                                    | 3.0  | -     | 5.0       | V             |
| Gate-Source Leakage                                       | $I_{GSS}$           | $V_{GS} = \pm 30\text{ V}$                                                                                                                            | -    | -     | $\pm 100$ | nA            |
| Zero Gate Voltage Drain Current                           | $I_{DSS}$           | $V_{DS} = 500\text{ V}$ , $V_{GS} = 0\text{ V}$                                                                                                       | -    | -     | 1         | $\mu\text{A}$ |
|                                                           |                     | $V_{DS} = 400\text{ V}$ , $V_{GS} = 0\text{ V}$ , $T_J = 125\text{ °C}$                                                                               | -    | -     | 10        |               |
| Drain-Source On-State Resistance                          | $R_{DS(on)}$        | $V_{GS} = 10\text{ V}$ , $I_D = 7\text{ A}$                                                                                                           | -    | 0.320 | 0.40      | $\Omega$      |
| Forward Transconductance <sup>a</sup>                     | $g_{fs}$            | $V_{DS} = 50\text{ V}$ , $I_D = 7\text{ A}$                                                                                                           | -    | 5.2   | -         | S             |
| <b>Dynamic</b>                                            |                     |                                                                                                                                                       |      |       |           |               |
| Input Capacitance                                         | $C_{iss}$           | $V_{GS} = 0\text{ V}$ ,<br>$V_{DS} = 100\text{ V}$ ,<br>$f = 1\text{ MHz}$                                                                            | -    | 1144  | -         | pF            |
| Output Capacitance                                        | $C_{oss}$           |                                                                                                                                                       | -    | 100   | -         |               |
| Reverse Transfer Capacitance                              | $C_{rss}$           |                                                                                                                                                       | -    | 12    | -         |               |
| Effective Output Capacitance, Energy Related <sup>a</sup> | $C_{o(er)}$         | $V_{GS} = 0\text{ V}$ , $V_{DS} = 0\text{ V to } 480\text{ V}$                                                                                        | -    | 87    | -         |               |
| Effective Output Capacitance, Time Related <sup>b</sup>   | $C_{o(tr)}$         |                                                                                                                                                       | -    | 125   | -         |               |
| Total Gate Charge                                         | $Q_g$               | $V_{GS} = 10\text{ V}$ , $I_D = 7\text{ A}$ , $V_{DS} = 400\text{ V}$                                                                                 | -    | 29    | 58        | nC            |
| Gate-Source Charge                                        | $Q_{gs}$            |                                                                                                                                                       | -    | 8     | -         |               |
| Gate-Drain Charge                                         | $Q_{gd}$            |                                                                                                                                                       | -    | 14    | -         |               |
| Turn-On Delay Time                                        | $t_{d(on)}$         | $V_{DD} = 400\text{ V}$ , $I_D = 7\text{ A}$ ,<br>$V_{GS} = 10\text{ V}$ , $R_g = 9.1\text{ }\Omega$                                                  | -    | 16    | 32        | ns            |
| Rise Time                                                 | $t_r$               |                                                                                                                                                       | -    | 27    | 54        |               |
| Turn-Off Delay Time                                       | $t_{d(off)}$        |                                                                                                                                                       | -    | 29    | 58        |               |
| Fall Time                                                 | $t_f$               |                                                                                                                                                       | -    | 26    | 52        |               |
| Gate Input Resistance                                     | $R_g$               | $f = 1\text{ MHz}$ , open drain                                                                                                                       | -    | 1.7   | -         | $\Omega$      |
| <b>Drain-Source Body Diode Characteristics</b>            |                     |                                                                                                                                                       |      |       |           |               |
| Continuous Source-Drain Diode Current                     | $I_S$               | MOSFET symbol showing the integral reverse p - n junction diode  | -    | -     | 14        | A             |
| Pulsed Diode Forward Current                              | $I_{SM}$            |                                                                                                                                                       | -    | -     | 56        |               |
| Diode Forward Voltage                                     | $V_{SD}$            | $T_J = 25\text{ °C}$ , $I_S = 7\text{ A}$ , $V_{GS} = 0\text{ V}$                                                                                     | -    | -     | 1.2       | V             |
| Reverse Recovery Time                                     | $t_{rr}$            | $T_J = 25\text{ °C}$ , $I_F = I_S = 7\text{ A}$ ,<br>$dI/dt = 100\text{ A}/\mu\text{s}$ , $V_R = 20\text{ V}$                                         | -    | 319   | -         | ns            |
| Reverse Recovery Charge                                   | $Q_{rr}$            |                                                                                                                                                       | -    | 3.0   | -         | $\mu\text{C}$ |
| Reverse Recovery Current                                  | $I_{RRM}$           |                                                                                                                                                       | -    | 18    | -         | A             |

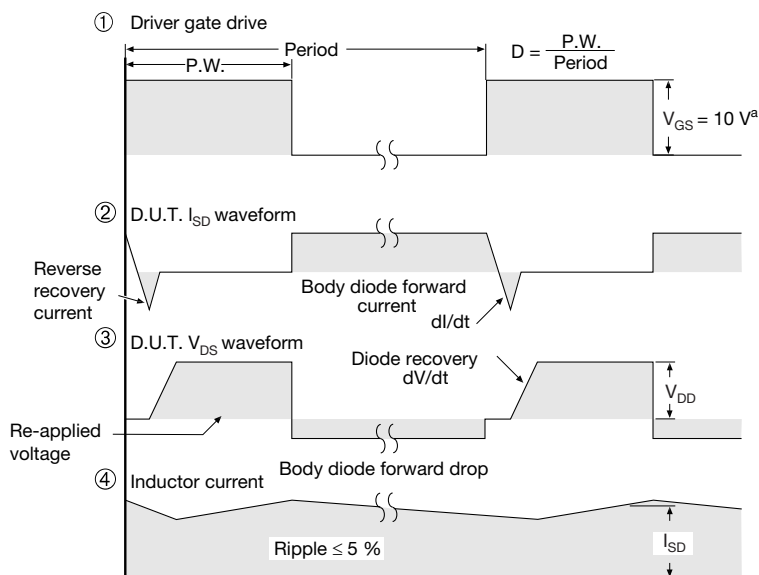
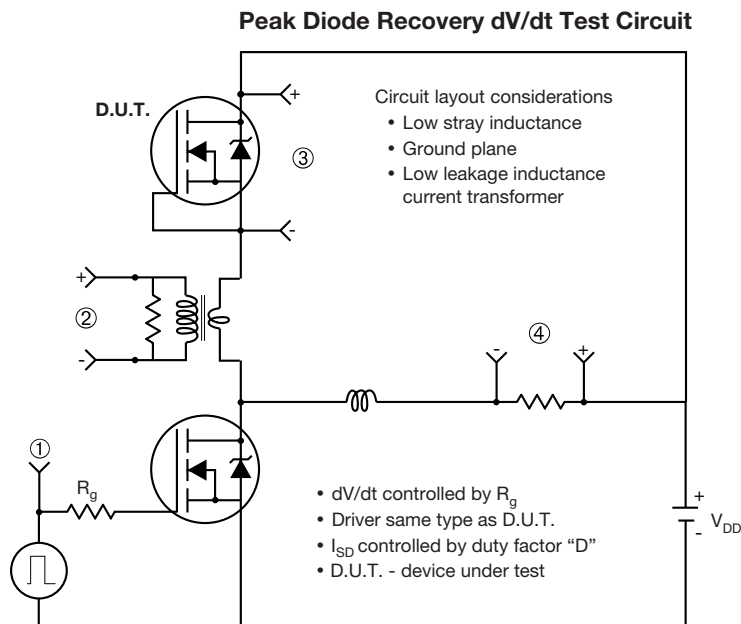
**Notes**

- a.  $C_{oss(er)}$  is a fixed capacitance that gives the same energy as  $C_{oss}$  while  $V_{DS}$  is rising from 0 % to 80 %  $V_{DSS}$ .  
b.  $C_{oss(tr)}$  is a fixed capacitance that gives the same charging time as  $C_{oss}$  while  $V_{DS}$  is rising from 0 % to 80 %  $V_{DSS}$ .

**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)

**Fig. 1 - Typical Output Characteristics**

**Fig. 4 - Normalized On-Resistance vs. Temperature**

**Fig. 2 - Typical Output Characteristics**

**Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage**

**Fig. 3 - Typical Transfer Characteristics**

**Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage**


**Fig. 7 - Typical Source-Drain Diode Forward Voltage**

**Fig. 9 - Maximum Drain Current vs. Case Temperature**

**Fig. 8 - Maximum Safe Operating Area**

**Fig. 10 - Temperature vs. Drain-to-Source Voltage**

**Fig. 11 - Normalized Thermal Transient Impedance, Junction-to-Case**


**Fig. 12 - Switching Time Test Circuit**

**Fig. 16 - Basic Gate Charge Waveform**

**Fig. 13 - Switching Time Waveforms**

**Fig. 17 - Gate Charge Test Circuit**

**Fig. 14 - Unclamped Inductive Test Circuit**

**Fig. 15 - Unclamped Inductive Waveforms**



**Fig. 18 - For N-Channel**

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## TO-220AB



| DIM.            | MILLIMETERS |       | INCHES |       |
|-----------------|-------------|-------|--------|-------|
|                 | MIN.        | MAX.  | MIN.   | MAX.  |
| A               | 4.25        | 4.65  | 0.167  | 0.183 |
| b               | 0.69        | 1.01  | 0.027  | 0.040 |
| b(1)            | 1.20        | 1.73  | 0.047  | 0.068 |
| c               | 0.36        | 0.61  | 0.014  | 0.024 |
| D               | 14.85       | 15.49 | 0.585  | 0.610 |
| E               | 10.04       | 10.51 | 0.395  | 0.414 |
| e               | 2.41        | 2.67  | 0.095  | 0.105 |
| e(1)            | 4.88        | 5.28  | 0.192  | 0.208 |
| F               | 1.14        | 1.40  | 0.045  | 0.055 |
| H(1)            | 6.09        | 6.48  | 0.240  | 0.255 |
| J(1)            | 2.41        | 2.92  | 0.095  | 0.115 |
| L               | 13.35       | 14.02 | 0.526  | 0.552 |
| L(1)            | 3.32        | 3.82  | 0.131  | 0.150 |
| $\varnothing P$ | 3.54        | 3.94  | 0.139  | 0.155 |
| Q               | 2.60        | 3.00  | 0.102  | 0.118 |

ECN: X12-0208-Rev. N, 08-Oct-12  
DWG: 5471

### Notes

- \*  $M = 1.32$  mm to  $1.62$  mm (dimension including protrusion)  
Heatsink hole for HVM
- Xi'an and Mingxin actual photo





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**Vishay Intertechnology, Inc. hereby certifies that all its products that are identified as Halogen-Free follow Halogen-Free requirements as per JEDEC JS709A standards. Please note that some Vishay documentation may still make reference to the IEC 61249-2-21 definition. We confirm that all the products identified as being compliant to IEC 61249-2-21 conform to JEDEC JS709A standards.**

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<http://moschip.ru/get-element>

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Нашей специализацией является поставка электронной компонентной базы двойного назначения, продукции таких производителей как XILINX, Intel (ex.ALTERA), Vicor, Microchip, Texas Instruments, Analog Devices, Mini-Circuits, Amphenol, Glenair.

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На всех этапах разработки и производства наши партнеры могут получить квалифицированную поддержку опытных инженеров.

Система менеджмента качества компании отвечает требованиям в соответствии с ГОСТ Р ИСО 9001, ГОСТ РВ 0015-002 и ЭС РД 009

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